



IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Jean-Michel Daga et al. PATENT APPLICATION
Serial No.: 10/810,033 Group Art Unit: 2816
Filed: March 26, 3004
For: HIGH EFFICIENCY, LOW COST, CHARGE PUMP CIRCUIT

Supplemental Information Disclosure Statement
with Certification under 37 CFR § 1.97(e)(1)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The following information is submitted in compliance with Applicants' duty of disclosure under 37 CFR § 1.97(e). A copy of the cited reference is enclosed.

Other Reference

Article entitled "A New High Efficiency CMOS Voltage Doubler" by Pierre Favrat et al., Swiss Federal Institute of Technology, Electronics Labs EL-LEG, Ecublens, CH-1015 Lausanne, Switzerland and Mead Microelectronics Engineering Applications and Design SA, Venoge 7, CH-1025 St. Sulpice, Switzerland, IEEE 1997 Custom Integrated Circuits Conference, pages 259-262, (0-7803-3669-0).

The undersigned hereby certifies that the item of information contained in this Supplemental Information Disclosure Statement was cited in a communication received from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

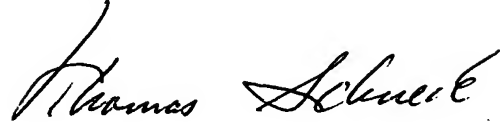
CERTIFICATE OF MAILING

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

Signed: Brenda Elmidolan
Typed Name: Brenda Elmidolan

Date: December 22, 2004

Respectfully submitted,



Thomas Schneck

Reg. No. 24,518

P.O. Box 2-E

San Jose, CA 95109-0005

(408) 297-9733

FORM PTO-1449

Atty. Docket No.
ATM-276Serial No.
10/810,033LIST OF PRIOR ART
CITED BY APPLICANTApplicants:
Jean-Michel Daga et al.Filing Date:
March 26, 2004

Group: 2816

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Publ. Date	Name	Class	Sub Class	Filing Date
AA						
AB						
AC						
AD						
AE						
AF						
AG						
AH						
AI						
AJ						

FOREIGN PATENT DOCUMENTS

Examiner Initial*	Document Number	Publ. Date	Country	Class	Sub Class	Translation Yes No
AK						
AL						
AM						
AN						

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AO	Article entitled "A New High Efficiency CMOS Voltage Doubler" by Pierre Favrat et al., Swiss Federal Institute of Technology Electronics Labs EL-LEG, Ecublens, CH-1015 Lausanne, Switzerland and Mead Microelectronics Engineering Applications and Design SA, Venoge 7, CH-1025 St. Sulpice, Switzerland, IEEE 1997 Custom Integrated Circuits Conference, pages 259-262 (0-7803-3669-0).
AP	

EXAMINER:

DATE CONSIDERED:

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.